



## **Description**

The XPX6411RD uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

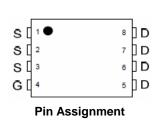
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

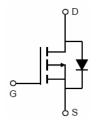
#### **Application**

- Load switch
- Battery protection

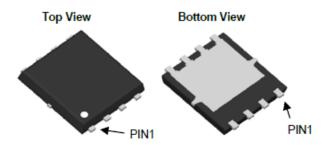
 $V_{DS}$  =-20V, $I_{D}$  =-120A  $R_{DS}(ON)$ =2.1 $m\Omega$ @ $V_{GS}$ =-4.5 $V_{CS}$ =-2.5 $V_{CS}$ 

 $RDS(ON)=3.8m\Omega@VGS=-1.8V$ 





Schematic diagram



#### **Package Marking and Ordering Information**

1		<u> </u>				
	Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
	XPX6411RD	XPX6411RD	DFN5X6-8L	-	-	5000

## Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

_ ,	•	•		
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-20	V	
Gate-Source Voltage	V <sub>G</sub> s	±10	V	
Drain Current-Continuous	I <sub>D</sub>	-120	Α	
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	-69.5	А	
Pulsed Drain Current	I <sub>DM</sub>	-340	А	
Maximum Power Dissipation	P <sub>D</sub>	130	W	
Derating factor		0.64	W/℃	
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$	
Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	R <sub>eJC</sub>	1.6	°C/W	



## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

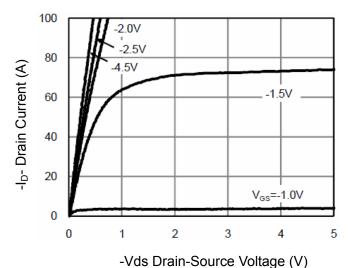
Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
rain-Source Breakdown Voltage BV <sub>DSS</sub>		V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-20	-	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)	·			•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.4	-0.6	-1.0	V	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-20A	-	2.1	2.5		
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-20A	-	2.8	3.6	mΩ	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-20A		3.8	8.0		
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-20A	100	-	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C <sub>lss</sub>	\/ - 40\/\/ -0\/	-	4950	-	PF	
Output Capacitance	Coss	$V_{DS}$ =-10V, $V_{GS}$ =0V, F=1.0MHz	-	380	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVIDZ	-	290	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t <sub>d(on)</sub>		-	20	-	nS	
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-10V, $R_{GEN}$ =3 $\Omega$	-	50	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =-4.5V,R <sub>L</sub> =0.5Ω	-	100	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	40	-	nS	
Total Gate Charge	Qg	V <sub>DS</sub> =-10V,I <sub>D</sub> =-20A,	-	100	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=-10V,I_{D}=-20A,$ $V_{GS}=-4.5V$	-	21	-	nC	
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> 4.5V	-	32	-	nC	
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-20A	-	-	-1.2	V	
Diode Forward Current (Note 2)	Is		-	-	-70	Α	
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = -10A	-	48	-	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	55	ı	nC	
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				y LS+LD)	

#### Notes:

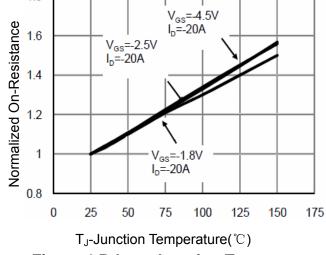
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



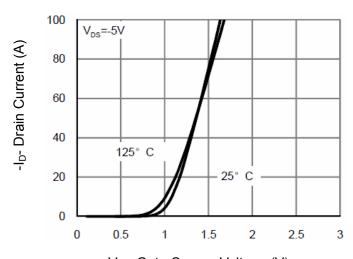
## Typical Electrical and Thermal Characteristics (Curves)



**Figure 1 Output Characteristics** 



**Figure 4 Rdson-Junction Temperature** 



-Vgs Gate-Source Voltage (V)

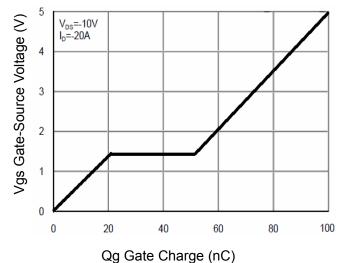


Figure 5 Gate Charge

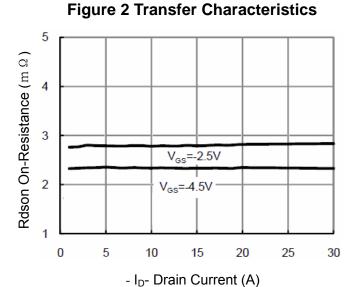


Figure 3 Rdson- Drain Current

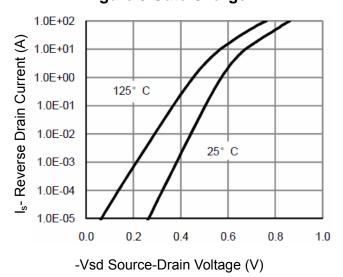


Figure 6 Source- Drain Diode Forward



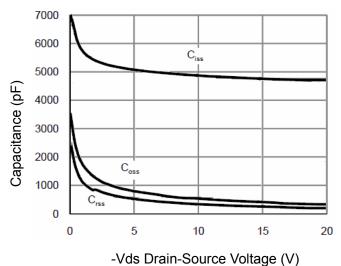
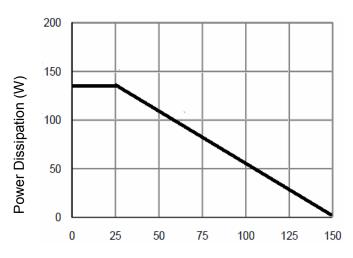
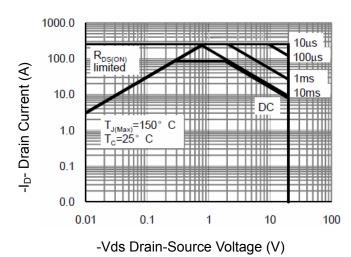


Figure 7 Capacitance vs Vds



 $T_J$ -Junction Temperature( ${}^{\circ}C$ )

# Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

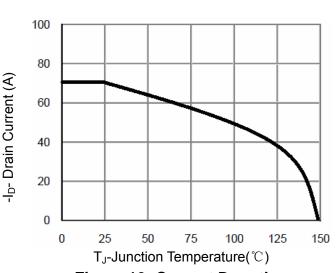
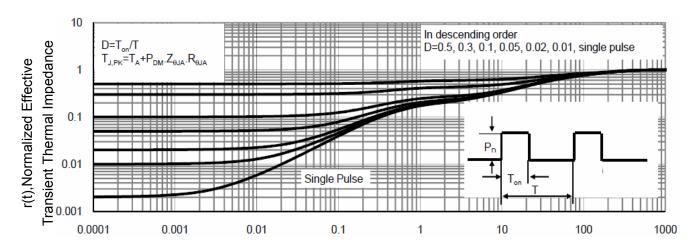


Figure 10 -Current De-rating

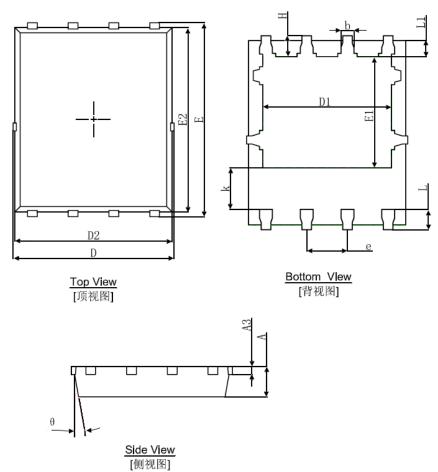


**Figure 11 Normalized Maximum Transient Thermal Impedance** 

Square Wave Pluse Duration(sec)



# **DFN5X6-8L Package Information**



Combal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	0.900	1.000	0.035	0.039	
A3	0.25	4REF.	0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
K	1.190	1.390	0.047	0.055	
b	0.035	0.450	0.014	0.018	
е	1.270(TYP.)		0.050(	TYP.)	
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	



#### Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time	
Pb device	<b>245</b> ℃ <b>±5</b> ℃	5sec±1sec	
Pb-Free device	260℃+0/-5℃	5sec±1sec	



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